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New Development in High Temperature Spring Probes

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### A Comparison of New Probe Materials Against Pb Free Solder

Nick Langston—Yamaichi Electronics USA Hideyuki Ichinosawa—Koshin Kogaku Co., Ltd.

### **Pb Free BGA Contactor - FA & Solutions**

Jiachun (Frank) Zhou, Kevin Deford—Interconnect Devices Inc.

### **New Probe Architecture in High Volume Production**

Tony DeRosa—Multitest

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# New Development in High Temperature Spring Probes

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2010 BiTS Workshop March 7 - 10, 2010































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## Conclusion

Successfully designed and developed a spring probe that will meet our current customer's high temperature test demands.

### **Probe Features**

- Excellent CRES performance at high temperature
- Improved current carrying capability
- Can easily be added to most probe designs

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# A Comparison Of New Probe Materials Against Pb Free Solder

Nick Langston Jr. Yamaichi Electronics, USA. Hideyuki Ichinosawa Koshin Kogaku Co., Ltd



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| Characteristics: Stability |                                 |  |  |  |  |  |  |  |  |
|----------------------------|---------------------------------|--|--|--|--|--|--|--|--|
|                            | Hardness<br>(Vickers)           | Resistivity<br>(μΩ / cm)   |  |  |  |  |  |  |  |
| Ni/Au                      | 450 /<br>200                    | 8.5 /<br>2.0   |  |  |  |  |  |  |  |
| PdCo                       | 630                             | 4.0  |  |  |  |  |  |  |  |
| DLC                        | 800                             | 500  |  |  |  |  |  |  |  |
| e Materials Against        | Dh Free Solder                  | 7  |  |  |  |  |  |  |  |
|                            | tics: S<br>Ni/Au<br>PdCo<br>DLC | tics: Stability<br>Hardness<br>(Vickers)<br>Ni/Au<br>450 /<br>200<br>PdCo<br>630<br>DLC<br>800 |  |  |  |  |  |  |  |





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| Test I  | Desig                         | jn      |         |       |
|---|-------------------------------|---------|---------|-------|
| <ul> <li>Apply 100mA current<br/>during cycling.</li> </ul>   | Total<br>Test<br>Time:        |         | 800mSec |       |
| Measure Contact     Resistance at every     cycle.  | Probe 1:<br>Supply<br>Current | 200mSec |         |       |
| Kelvin 4 wire     measurement   | Probe 2:<br>Supply<br>Current |         | 200mSec |       |
| <ul> <li>If Cres &gt; 500mΩ, clean<br/>with Mipox (2 touchdowns)</li> <li>If cleaning required 5x<br/>within 100 cycles, end test.</li> </ul> | Probe 3:<br>Supply<br>Current |         | 20      | 0mSec |





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# Pb Free BGA Contactor -FA & Solutions

Jiachun Zhou (Frank) Kevin DeFord Interconnect Devices, Inc.



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### Macro & Micro Analysis Comparing to reference area, major elements at contaminated area is Sn & O. No Au is detected. C08V391820.spe: V1 (pin #1) EAG(CA 2008 Oct 8 10.0 keV 0 FRR 6.2340e+004 max 7.95min **Contaminated area** C08V391810.spe c 10 (visible at macro) Sample V1 residue on tip as-rec'd surface c/s Reference area Sample V1 eference area 50.0µr a С 1800 2000 400 600 1000 1200 1400 Kinetic Energy (eV) 1600 2200 200 800 3/2010 Pb Free BGA Contactor - FA & Solutions



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# Macro & Micro Analysis

 Sn & O have same distribution along contamination layer. SnxOy must be the major contaminates stuck on crown surface to cause high Cres.
 Test temperature can affect formation and growth of SnxOy.



# Solution: Crown Structure





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| S   | olution:  | Cleanin   | g  |
|---|---|---|--|
| Cleaning Kit  | 1. Rotary Tool<br>2. Rotary Tool Brushes<br>3. Hand Brush<br>4. Saturated Cleaning Cloth<br>5. Sacrificial Device<br>6. Scissors<br>8. Latex or Nitrile Gloves<br>6 | <text><list-item><list-item></list-item></list-item></text> | <section-header></section-header>  |
| Step 3-1  |   | Step 3-2  | Step 4   |
| <ul> <li>Put trimmed cloth into packet and ensure to</li> <li>Use a sacrificed package as cover cloth.</li> </ul> | cover all tip; • Put lid o<br>• If no lid,  | n socket;<br>cycle package 10 times.                        | <ul> <li>Saturated cloth to soak over 20 min.</li> <li>Longer soak time no detrimental to<br/>socket performance.</li> </ul> |
|   |   |   |  |
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# **New Probe Architecture in High Volume Production**

**Tony DeRosa Multitest** 



March 7 - 10, 2010







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# Agenda

- Challenges from Packaging & Device Advancements
- Contactor Performance Requirements
- Flat Probe Technology Advantages
- High Volume Production (HVP) Test Results
- Summary



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# Challenges from Packaging & Device Advancements

Packaging innovation & Device Complexity

- Fine pitch 0.4mm today, 0.3mm on it's way
- RF requirements high bandwidth, low inductance

WLCSP Package

- SOC System on Chip
- WLCSP Wafer Level CSP
- POP Package on Package



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# High Volume Production HVP Contactor Performance Requirements



performance from lower quality components

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| Summary of Specifications  |                         |                    |         |  |  |  |  |  |  |
|--|-------------------------|--------------------|---------|--|--|--|--|--|--|
|  | <u>MER040</u>           | <u>MER080</u>      |         |  |  |  |  |  |  |
| Probe Test Height  | 3.3 mm                  | 3.3 mm             | 3.8 mm  |  |  |  |  |  |  |
| Probe Compliance   | 0.43 mm                 | 0.48 mm            | 0.57 mm |  |  |  |  |  |  |
| Force - Test Height  | 30g                     | 30g                | 30g     |  |  |  |  |  |  |
| Bandwidth -1dB*  | 18 GHz                  | 20 GHz             | 18 GHz  |  |  |  |  |  |  |
| Inductance*  | 0.98 nH                 | 1.16 nH            | 1.43 nH |  |  |  |  |  |  |
| Contact Resistance   |                         | < 80 mOhm          |         |  |  |  |  |  |  |
| Life   | :                       | > 500,000 (typical | )       |  |  |  |  |  |  |
| * Bandwidth and inductance are measured at native pitch, GSG in Vespel ** New<br>Probe |                         |                    |         |  |  |  |  |  |  |
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# High Volume Test Results Device 1

- 407 BGA, 0.5 mm pitch, 12x12 mm
- Application: EDGE/GPRS/GSM Cellular Processor
  - Integrated RF transceiver
  - Mixed signal analog
- Key Test parameter: Signal-to-Noise Ratio (SNR)

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# High Volume Test Results Device 1

|                    | Mercury | Probe B |
|--------------------|---------|---------|
| Insertion Life     | 600k +  | 300k    |
| First Pass Yield   | 90+%    | 80+%    |
| Cleaning Intervals | 40K     | 20k     |

Similar results were achieved with 28 Mercury contactors at multiple test houses

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# High Volume Test Results Device 1

Why did Mercury outperform the competition?

- Better contact
  - Sharp edge contact to solder ball
  - Better tip wear
  - Better plating

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### **High Speed Performance Device 2** Results: Test Parameter – Input Voltage (lower is better) Probe C requires 420 mV for consistent passes -MER050 requires only 360 mV for consistent passes -Improved performance due to higher bandwidth contactor PASS • MER050 length, impedance match contribute to FAIL higher bandwidth MER050 Shmoo Plot PROBE C Shmoo Plot 500 Voltage (mV) Input Voltage (mV) 400 400 350 350 nput 300 300 250 -300 Waveform Offset (ppm) Waveform Offset (ppm) 03/2010 New Probe Architecture in High Volume Production 20





# **RF Characterization Device 3**

- •121BGA, 1.0mm pitch, 12x12mm
- Dual-Channel 10 GBE SFI-TO-XFI (10-Gigabit serial electrical interface) with Electronic Dispersion Compensation (EDC) equalizer
- •One DUT is used as signal source
- DUT TX (SFI+) sends PRBS7 pattern at 10.3125Gbs



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# **RF Characterization Device 3**MER080 outperforms probe A through 10GHz

- Typically ~10% better insertion loss
- Up to 18% improvement

|               |                |                 |      |       |   | Ir | nserti | on Lo     | ss - M            | ER080           | ) vs "F       | ROBE          | A"           |
|---------------|----------------|-----------------|------|-------|---|----|--------|-----------|-------------------|-----------------|---------------|---------------|--------------|
| Freq<br>(GHz) | MER080<br>(dB) | PROBE A<br>(dB) | Δ%   | 0     | ~ |    | 7      | $\frown$  |                   | ~               |               |               |              |
| 1             | -0.1           | -0.5            | 4.4  | - 2   |   |    | ~      |           | $\langle \rangle$ | $\mathcal{A}$   | $\backslash$  | $\wedge$      |              |
| 2             | -1.2           | -1.5            | 3.0  | 3     | - |    |        | $\sim$    | $\forall \forall$ | $/ \rightarrow$ | $\rightarrow$ | $\rightarrow$ | $\mathbf{t}$ |
| 3             | -0.7           | -2.6            | 18.1 | œ ⁴   | - | -  |        | 00        | ~                 | ·               | $H^{-}$       | $+ \wedge$    | +            |
| 4             | -2.5           | -3.7            | 9.7  | p) ss | - |    | PROB   | 80<br>F A |                   |                 | $\mathcal{H}$ | H             | H            |
| 5             | -1.7           | -2.1            | 3.7  | 3 %   | - | _  |        |           |                   |                 | ľ             | <u>/</u>      | +            |
| 6             | -4.3           | -5.6            | 8.5  | -7    | - |    |        |           |                   |                 |               |               | +            |
| 7             | -3.2           | -5              | 12.9 | -8    | - |    |        |           |                   |                 |               |               |              |
| 8             | -5.7           | -7.4            | 9.2  | -9    |   |    |        |           |                   |                 |               |               |              |
| 9             | -8             | -12             | 14.7 | -10   |   |    |        |           |                   |                 |               |               |              |
| 10            | -26.2          | -26.7           | 0.3  |       | D | 1  | 2      | 3         | 4<br>Frea         | 5<br>uencv      | 6<br>(GHz)    | 7             | 8            |
|               |                |                 |      |       |   |    |        |           |                   | ,               | ()            |               |              |
|               |                |                 |      |       |   |    |        |           |                   |                 |               |               |              |

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